

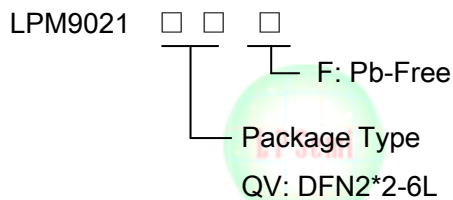


Single P-Channel, -12V, -6.5A, Power MOSFET

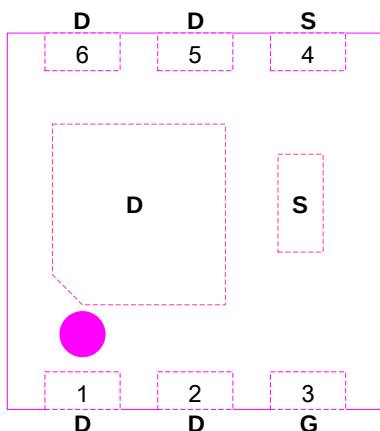
General Description

The LPM9021 is P-Channel enhancement MOSFET Effect Transistor. It uses advanced trench technology and design to provide excellent RDS (ON) with low gate charge. This device is suitable for using in DC-DC conversion, power switch and charging circuit. Standard Product LPM9021QVF is Pb-free and Halogen-free.

Order Information



Pin Configurations



Features

- Trench Technology
- Super high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package DFN2*2-6L

Applications

- ✧ Driver for Relay, Solenoid, Motor, LED etc.
- ✧ DC-DC converter circuit
- ✧ Power Switch
- ✧ Load Switch
- ✧ Charging

Marking Information

Device	Marking	Package	Shipping
LPM9021QVF		DFN2*2-6L	3K/REEL

Pin Description

Pin Number	Pin Description
1,2	Drain Pin
3	Gate Pin
4	Source Pin
5,6	Drain Pin



Absolute Maximum Ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		VDS	-12		V
Gate-Source Voltage		VGS	±12		
Continuous Drain Current	TA=25°C	ID	-6.5	-5.6	A
	TA=70°C		-5.2	-4.4	
Maximum Power Dissipation	TA=25°C	PD	1.9	1.4	W
	TA=70°C		1.2	0.9	
Continuous Drain Current	TA=25°C	ID	-4.8	-3.9	A
	TA=70°C		-3.8	-3.9	
Maximum Power Dissipation	TA=25°C	PD	1.0	0.6	W
	TA=70°C		0.6	0.4	
Pulsed Drain Current c		IDM	-24		A
Operating Junction Temperature		TJ	150		°C
Lead Temperature		TL	260		°C
Storage Temperature Range		Tstg	-55 to 150		°C

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	t ≤ 10 s	R _{θJA}	49	64	°C/W
	Steady State		66	88	
Junction-to-Ambient Thermal Resistance	t ≤ 10 s	R _{θJA}	84	118	
	Steady State		125	180	
Junction-to-Case Thermal Resistance	Steady State	R _{θJC}	32	42	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR-4 board using minimum pad size, 1oz copper

c Pulse width < 380 μs, Duty Cycle < 2%

d Maximum junction temperature T_J = 150°C.

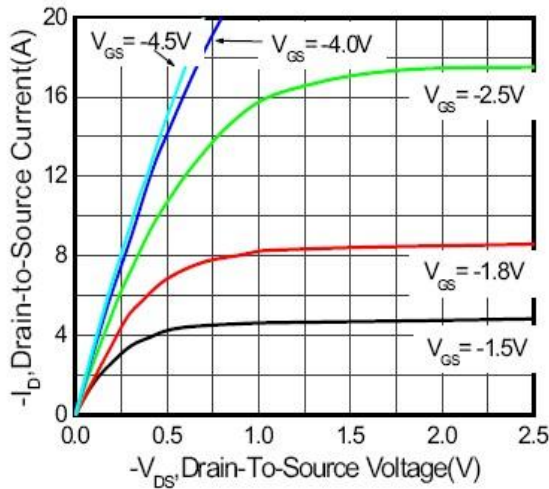


Electrical Characteristics

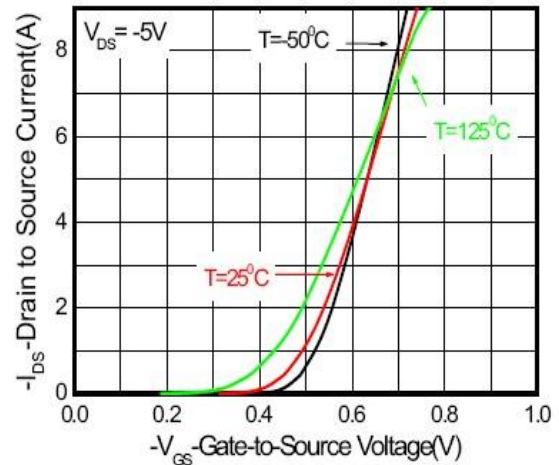
Parameter	Symbol	Test Condition	Min	Typ.	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = -250uA	-12			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V, V _{GS} = 0V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = □12V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-0.4	-0.52	-0.9	V
Drain-to-source On-resistance b, c	R _{DS(on)}	V _{GS} = -4.5V, I _D = -5.5A		23	29	mΩ
		V _{GS} = -2.5V, I _D = -2.5A		30	39	
		V _{GS} = -1.8V, I _D = -1.8A		39	50	
		V _{GS} = -1.5V, I _D = -1.5A		48	90	
Forward Transconductance	g _{FS}	V _{DS} =-5.0V, I _D =-5.5A		23		S
CAPACITANCES, CHARGES						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz V _{DS} = -10 V		1970		pF
Output Capacitance	C _{OSS}			205		
Reverse Transfer Capacitance	C _{RSS}			195		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -4.5 V, V _{DS} = -10 V, I _D = -6.5A		21.0		nC
Threshold Gate Charge	Q _{G(TH)}			0.95		
Gate-to-Source Charge	Q _{GS}			1.30		
Gate-to-Drain Charge	Q _{GD}			7.60		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V _{GS} = -4.5 V, V _{DD} = -10 V, I _D =-6.5A, R _G =6 □		16		ns
Rise Time	tr			15.5		
Turn-Off Delay Time	td(OFF)			78		
Fall Time	tf			44		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S =-1.0A	-	-0.76	1.5	V



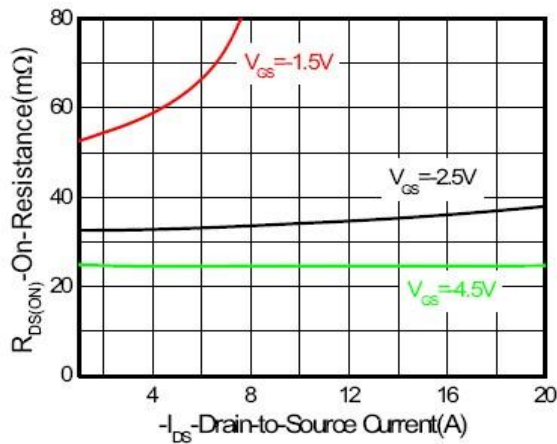
Typical Characteristics (Ta=25°C, unless otherwise noted)



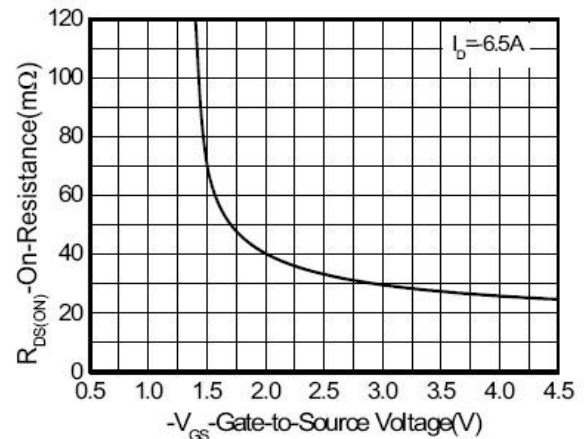
Output characteristics



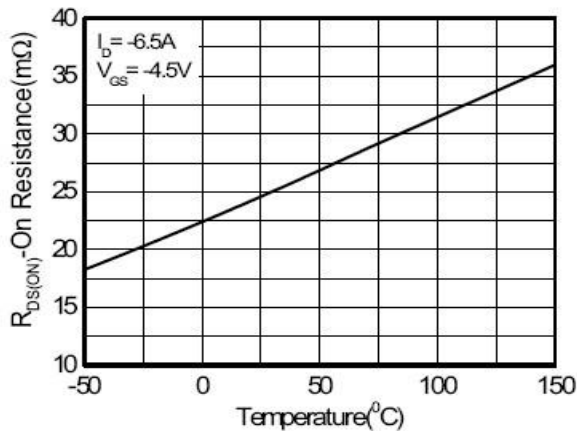
Transfer characteristics



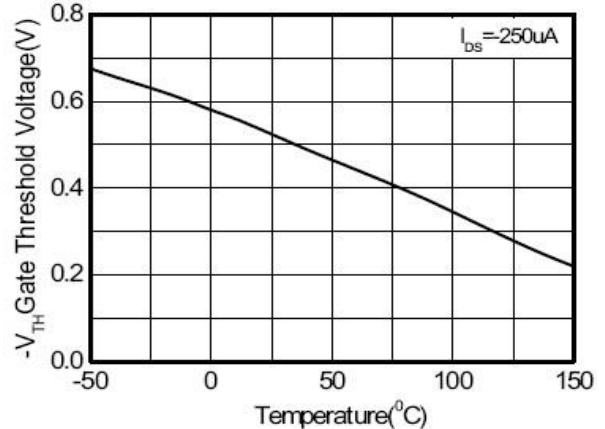
On-Resistance vs. Drain current



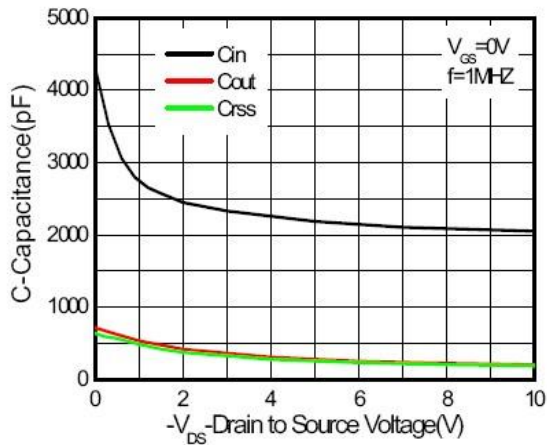
On-Resistance vs. Gate-to-Source voltage



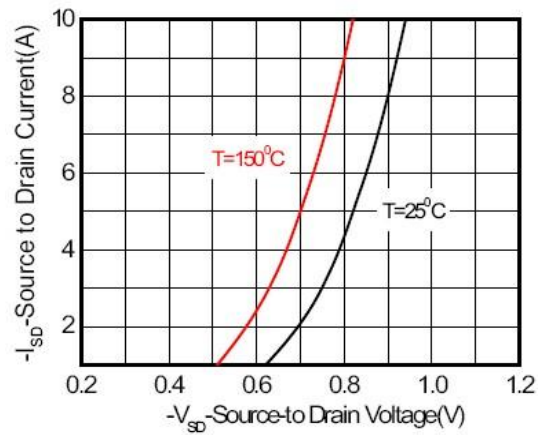
On-Resistance vs. Junction temperature



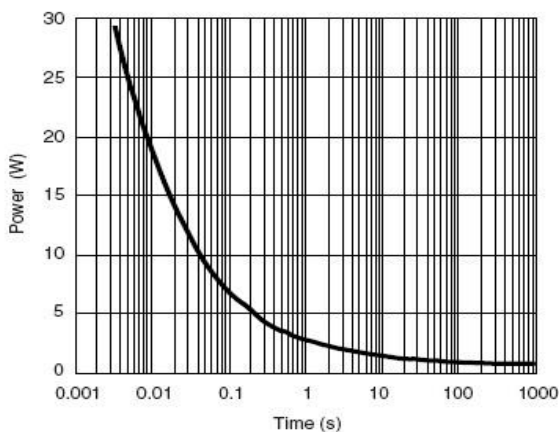
Threshold voltage vs. Temperature



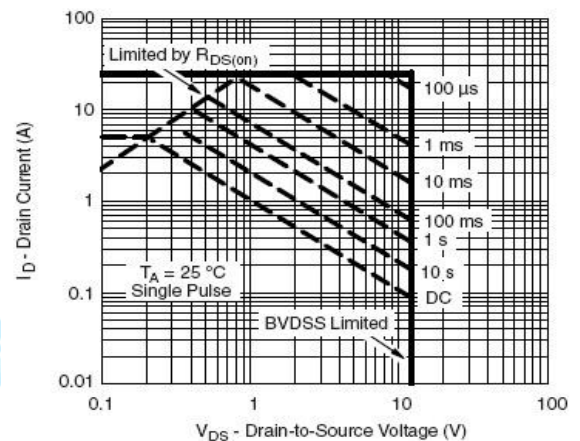
Capacitance



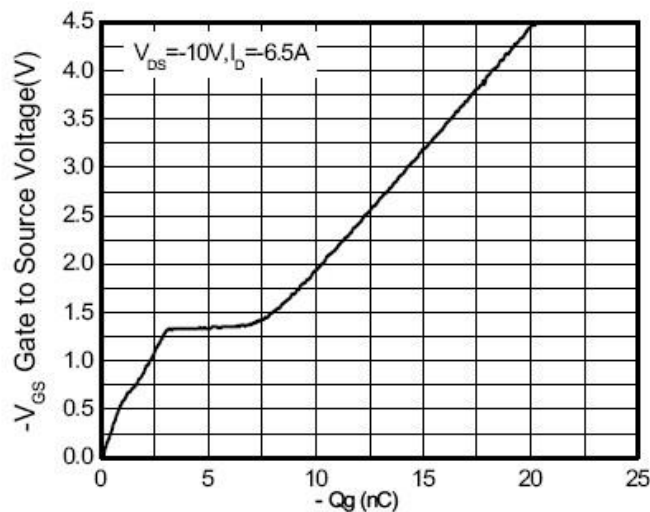
Body diode forward voltage



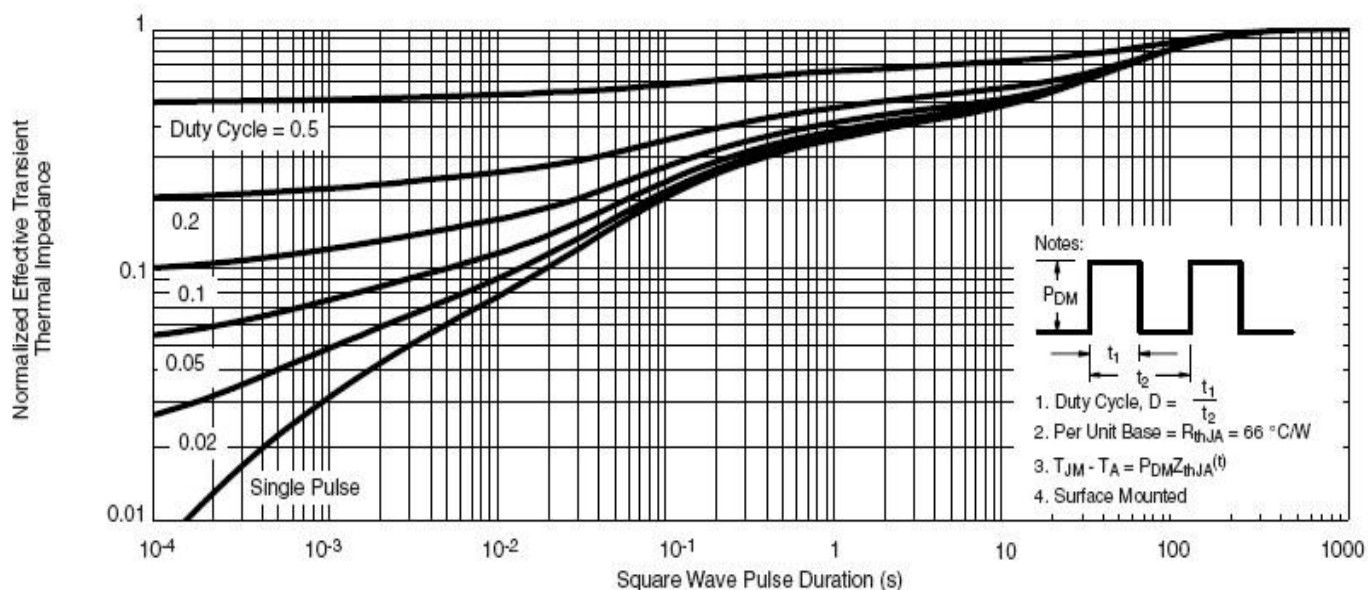
Single pulse power



Safe operating power



Gate Charge Characteristics

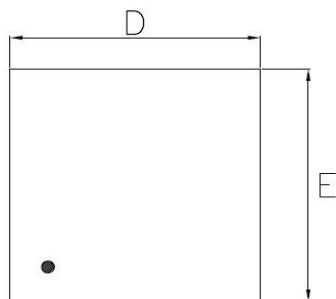


Transient thermal response (Junction-to-Ambient)

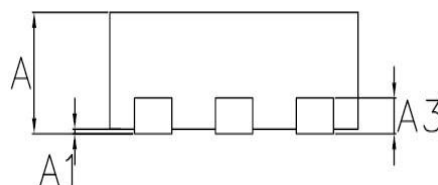




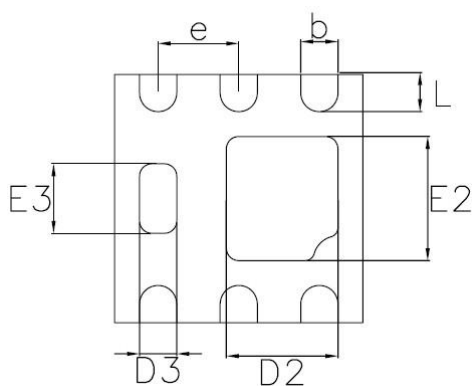
Packaging Information



Top View



Side View



Bottom View

Symbol	Dimensions in millimeter		
	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.203 Ref.		
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D2	0.85	0.90	0.95
E2	0.75	0.80	0.85
D3	0.25	0.30	0.35
E3	0.51	0.56	0.61
b	0.25	0.30	0.35
L	0.30	0.35	0.40
e	0.65 BSC.		